

Application No.: 09/787,661

page 5, line 21: after "than" insert ~~--it would be--~~;

line 25: cancel "later";

page 6, line 2: cancel "wet" and after "chemically" insert ~~--wet--~~;

line 28: after "structure" insert ~~--and--~~; and

page 7, line 1: correct "for" to ~~--of--~~.

In the Claims:

Cancel claims 1 - 3 and substitute the following new claims therefor:

A₂
4. (New) A method of fabricating on an insulating region an amorphous or polycrystalline silicon germanium layer of increased thickness, homogeneity, uniform grain size distribution and reduced surface roughness, comprising the step of:

providing a seed initiation layer of good seeding capacity and insulating properties between the insulating region and the amorphous or polycrystalline silicon germanium layer.

5. (New) The method of claim 4, wherein the amorphous or polycrystalline layer contains a diffusion inhibiting agent.

6. (New) The method of claim 5, wherein the diffusion inhibiting agent is an element from the group consisting of carbon and oxygen.

7. (New) The method of claim 4, wherein the insulating region comprises a SiO₂-layer.

8. (New) The method of claim 4, wherein the seed initiation layer comprises